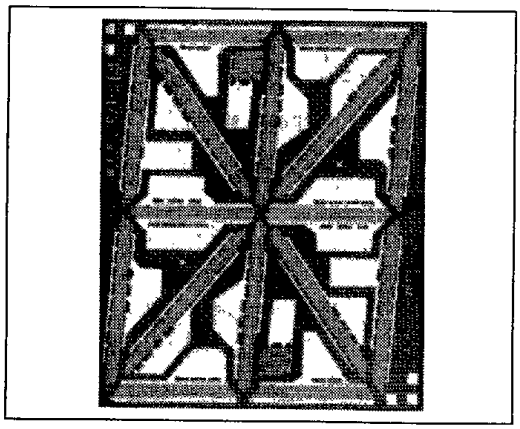
SIEMENS

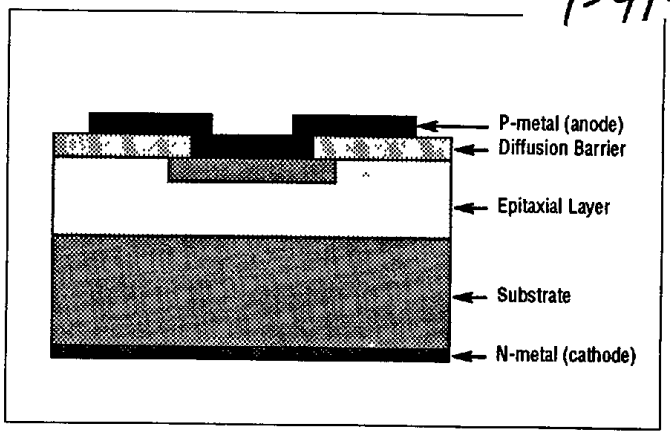
RM-81B
Mask-Diffused GaAsP Monolithic LED

Custom Optoelectronic Products

PART NO. 2680-0056

T-41-99





DESCRIPTION

Siemens RM-81B is a mask-diffused GaAsP monolithic light-emitting diode. With a bright and uniform 655 nm emission, this device is ideal for display applications.

MATERIAL

Epitaxial Layer:	$GaAs_{1-x}P_x$: Te	
Substrate:	GaAs : Si or GaAs : Te	
Metalizations:	Anode	Aluminum
	Cathode	Gold-Germanium
Dimensions (center to center):	Height	0.135″
	Width	0.112″
	Thickness	0.010″

TYPICAL DEVICE PARAMETERS

Forward I-V Characteristics	V_{F3}	1.59 V	@ 20 mA
	V_{F2}	1.57 V	@ 10 mA
	V_{F1}	1.40 V	@ 100 µA
Reverse I-V Characteristics	V_{R1}	-23.0 V	@ -10 µA
Peak EL Wavelength	λ	655 nm	@ 20 mA
Spectral Half-Width	FWHM	40 nm	@ 20 mA
Luminous Intensity (Device does not have AR coating)	LI	220 µCd	@ 10 mA